

L Number	Hits	Search Text	DB	Time stamp
-	7839	ferroelectric with memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 15:18
-	1256	(ferroelectric with memory) and (memory near3 array)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 09:48
-	850	((ferroelectric with memory) and (memory near3 array)) and electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 09:49
-	502	((((ferroelectric with memory) and (memory near3 array)) and electrode) and dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 09:50
-	167	(((((ferroelectric with memory) and (memory near3 array)) and electrode) and dielectric) and peripheral	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 09:51
-	167	((((((ferroelectric with memory) and (memory near3 array)) and electrode) and dielectric) and peripheral) and circuit	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 09:52
-	63	((((((((ferroelectric with memory) and (memory near3 array)) and electrode) and dielectric) and peripheral) and circuit) and intersect\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 09:52
-	56	(((((((((ferroelectric with memory) and (memory near3 array)) and electrode) and dielectric) and peripheral) and circuit) and (intersection intersecting)	USPAT; US-PGPUB; EPO; JPO;	2002/10/21 09:53
-	56	((((((((((ferroelectric with memory) and (memory near3 array)) and electrode) and dielectric) and peripheral) and circuit) and intersect\$4) and (((((((ferroelectric with memory) and (memory near3 array)) and electrode) and dielectric) and peripheral) and circuit) and (intersection intersecting))	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 09:53
-	53	((((((((((ferroelectric with memory) and (memory near3 array)) and electrode) and dielectric) and peripheral) and circuit) and intersect\$4) and (((((((ferroelectric with memory) and (memory near3 array)) and electrode) and dielectric) and peripheral) and circuit) and (intersection intersecting)))) and direction	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 15:02
-	28	"5060191"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 15:04
-	25	"5060191" and ferroelectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 15:39

-	23	("5060191" and ferroelectric) and electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 15:05
-	22	((("5060191" and ferroelectric) and electrode) and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 15:06
-	10	((("5060191" and ferroelectric) and electrode) and memory) and peripheral	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 15:07
-	443	(ferroelectric with memory) and (peripheral with (section region area circuit))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 15:21
-	387	((ferroelectric with memory) and (peripheral with (section region area circuit))) and (electrode dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 15:22
-	265	((((ferroelectric with memory) and (peripheral with (section region area circuit))) and (electrode dielectric)) and (ferroelectric with electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 15:40
-	260	(((((ferroelectric with memory) and (peripheral with (section region area circuit))) and (electrode dielectric)) and (ferroelectric with electrode)) and (cell array device))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 15:41
-	49	((((((ferroelectric with memory) and (peripheral with (section region area circuit))) and (electrode dielectric)) and (ferroelectric with electrode)) and (cell array device)) and strip\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 15:42